

Silicon PNP Power Transistors

2SB946

DESCRIPTION

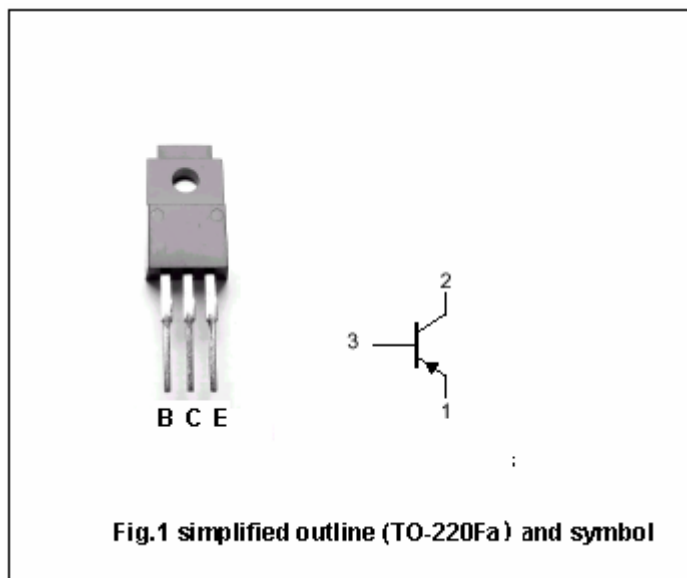
- With TO-220Fa package
- Complement to type 2SD1271
- Low saturation voltage
- Good linearity of h_{FE}
- High current

APPLICATIONS

- For power switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-130	V
V_{CEO}	Collector-emitter voltage	Open base	-80	
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current (DC)		-7	A
I_{CM}	Collector current-Peak		-15	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	40	W
		$T_a=25^\circ\text{C}$	2	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon PNP Power Transistors

2SB946

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10mA$, $I_B = 0$	-80			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -5A$; $I_B = -0.25A$			-0.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -5A$; $I_B = -0.25A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -100V$; $I_E = 0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V$; $I_C = 0$			-50	μA
h_{FE-1}	DC current gain	$I_C = -0.1A$; $V_{CE} = -2V$	45			
h_{FE-2}	DC current gain	$I_C = -3A$; $V_{CE} = -2V$	60		260	
f_T	Transition frequency	$I_C = -0.5A$; $V_{CE} = -10V$		30		MHz

Switching times

t_{on}	Turn-on time	$I_C = -3A$; $I_{B1} = -0.3A$ $I_{B2} = 0.3A$		0.5		μs
t_s	Storage time			1.5		μs
t_f	Fall time			0.1		μs

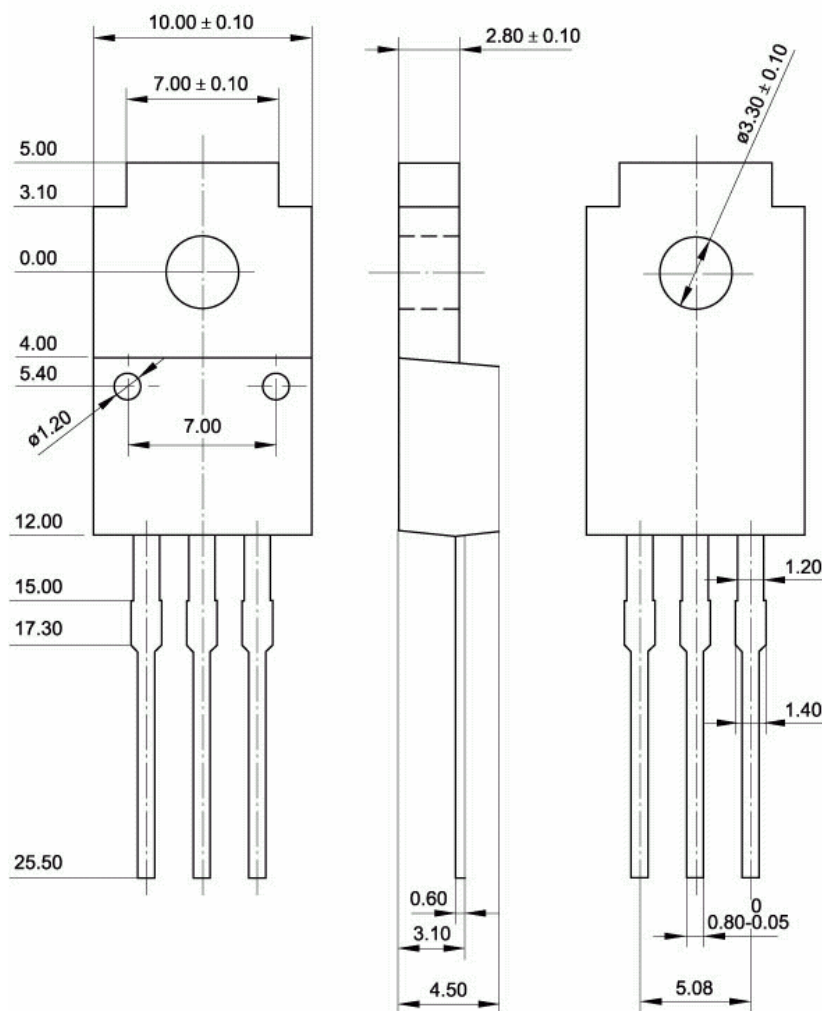
◆ h_{FE-2} Classifications

R	Q	P
60-120	90-180	130-260

Silicon PNP Power Transistors

2SB946

PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

Silicon PNP Power Transistors

2SB946

